Tool ID: 107
Tool Location: 103

**Equipment Information Sheet**

# B3 - LPCVD LTO

**Manager: Phil Infante 607-254-4926**
**Backup: Aaron Windsor 607-254-4831**

Calls to staff phones will be automatically forwarded to their cell phones during accessible hours. At other times leave a message or send them an email.

## SAFETY

- The furnaces are run at elevated temperatures of 400-1200°C and use flammable, toxic, and corrosive gases.

## USAGE RESTRICTIONS

- No changing of gas flows or process parameters without staff approval
- Max temperature of 450 C

## SCHEDULING/SIGN-UP RESTRICTIONS

*Minimum Tool Time: 90 minutes*

- Reservation blocks greater than 8 hrs must be cleared by a MOS staff person prior to reserving the time

## MATERIALS COMPATIBILITY CATEGORY

**Tool Category 1E: Silicon Based Materials and Select Dieletrics**

| Allowed | Not Allowed |
|---|---|
| Silicon Based Materials only | No Evaporated or Sputtered Films |
| Si, SiC, $SiO_2$ substrates | No Metal or Organic Films |
| All Furnace grown or deposited films | No Glass Substrates |
| PECVD Films | No III/V Compound Semiconductors |
| Select ALD dieletrics ($SiO_2$, SiN, $HfO_2$, HFN) | No High Vapor pressure materials |
| Spin on Glass and Spin on Dopants | Organic/Biology Molecules prepared-with or without Salt buffers |

**High Vapor Pressure Metals and Compounds are materials that have a vapor pressure above 1e-6 Torr at 400 C.**

## Additional Material Restrictions and Exceptions

- MOS CLEAN required prior to use
- Only use designated MOS holders, wands and tweezeers

*Last Updated: 04/10/2026*